

# Thomas Seyller

## List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

191 papers	18,971 citations	58 h-index	137 g-index
199 ext. papers	20,602 ext. citations	5.2 avg, IF	6.31 L-index

#	Paper	IF	Citations
191	Hardness Enhancement in CoCrFeNi <sub>1-x</sub> (WC) <sub>x</sub> High-Entropy Alloy Thin Films Synthesised by Magnetron Co-Sputtering. <i>Coatings</i> , <b>2022</b> , 12, 269	2.9	
190	Ultrafast electronic linewidth broadening in the C 1s core level of graphene. <i>Physical Review B</i> , <b>2021</b> , 104,	3.3	3
189	Influence of Nanoarchitectures on Interlayer Interactions in Layered Bi <sub>2</sub> MoSe Heterostructures. <i>Journal of Physical Chemistry C</i> , <b>2021</b> , 125, 9469-9478	3.8	3
188	CoCrFeNi High-Entropy Alloy Thin Films Synthesised by Magnetron Sputter Deposition from Spark Plasma Sintered Targets. <i>Coatings</i> , <b>2021</b> , 11, 468	2.9	4
187	Challenging the Durability of Intermetallic Mo-Ni Compounds in the Hydrogen Evolution Reaction. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2021</b> , 13, 23616-23626	9.5	5
186	Stacking Relations and Substrate Interaction of Graphene on Copper Foil. <i>Advanced Materials Interfaces</i> , <b>2021</b> , 8, 2002025	4.6	1
185	Synthesis and Electrical Properties of a New Compound (BiSe) <sub>0.97</sub> (Bi <sub>2</sub> Se <sub>3</sub> ) <sub>1.26</sub> (BiSe) <sub>0.97</sub> (MoSe <sub>2</sub> ) Containing Metallic 1T-MoSe <sub>2</sub> . <i>Chemistry of Materials</i> , <b>2021</b> , 33, 6403-6411	9.6	2
184	Electronic band structure of Bi-intercalate layers in graphene and SiC(0001). <i>Journal of the Korean Physical Society</i> , <b>2021</b> , 78, 157-163	0.6	0
183	Annealing effects on a-SiC:H and a-SiCN:H films deposited by plasma CVD methods. <i>Vacuum</i> , <b>2020</b> , 178, 109410	3.7	1
182	From a Cerium-Doped Polynuclear Bismuth Oxido Cluster to BiO:Ce. <i>Inorganic Chemistry</i> , <b>2020</b> , 59, 3353-3366	5.1	11
181	Substrate induced nanoscale resistance variation in epitaxial graphene. <i>Nature Communications</i> , <b>2020</b> , 11, 555	17.4	14
180	Production and processing of graphene and related materials. <i>2D Materials</i> , <b>2020</b> , 7, 022001	5.9	179
179	Silicon Carbide Stacking-Order-Induced Doping Variation in Epitaxial Graphene. <i>Advanced Functional Materials</i> , <b>2020</b> , 30, 2004695	15.6	9
178	Electronic structure of designed [(SnSe) <sub>1-x</sub> Te <sub>x</sub> ]/[TiSe <sub>2</sub> ] <sub>2</sub> heterostructure thin films with tunable layering sequence. <i>Journal of Materials Research</i> , <b>2019</b> , 34, 1965-1975	2.5	2
177	Growth of Nanocrystalline MoSe <sub>2</sub> Monolayers on Epitaxial Graphene from Amorphous Precursors (Phys. Status Solidi B 2/2019). <i>Physica Status Solidi (B): Basic Research</i> , <b>2019</b> , 256, 1970015	1.3	
176	Surfaces, Interfaces, and Nanostructures: Spectroscopic Characterization and Applications. <i>Physica Status Solidi (B): Basic Research</i> , <b>2019</b> , 256, 1900027	1.3	
175	Synthesis and Properties of (BiSe) <sub>0.97</sub> MoSe <sub>2</sub> : A Heterostructure Containing Both 2H-MoSe <sub>2</sub> and 1T-MoSe <sub>2</sub> . <i>Chemistry of Materials</i> , <b>2019</b> , 31, 5824-5831	9.6	11

174	Quasi-Freestanding Graphene on SiC(0001) by Ar-Mediated Intercalation of Antimony: A Route Toward Intercalation of High-Vapor-Pressure Elements. <i>Annalen Der Physik</i> , <b>2019</b> , 531, 1900199	2.6	6
173	Growth of Nanocrystalline MoSe <sub>2</sub> Monolayers on Epitaxial Graphene from Amorphous Precursors. <i>Physica Status Solidi (B): Basic Research</i> , <b>2019</b> , 256, 1800283	1.3	1
172	Charge transfer in (PbSe) (NbSe) and (SnSe) (NbSe) ferecrystals investigated by photoelectron spectroscopy. <i>Journal of Physics Condensed Matter</i> , <b>2018</b> , 30, 055001	1.8	4
171	Extremely flat band in bilayer graphene. <i>Science Advances</i> , <b>2018</b> , 4, eaau0059	14.3	59
170	Direct observation of grain boundaries in graphene through vapor hydrofluoric acid (VHF) exposure. <i>Science Advances</i> , <b>2018</b> , 4, eaar5170	14.3	19
169	Work function of graphene multilayers on SiC(0001). <i>2D Materials</i> , <b>2017</b> , 4, 015043	5.9	39
168	Growth and Intercalation of Graphene on Silicon Carbide Studied by Low-Energy Electron Microscopy. <i>Annalen Der Physik</i> , <b>2017</b> , 529, 1700046	2.6	10
167	Single Crystalline Metal Films as Substrates for Graphene Growth. <i>Annalen Der Physik</i> , <b>2017</b> , 529, 17000236		4
166	Terahertz ratchet effects in graphene with a lateral superlattice. <i>Physical Review B</i> , <b>2016</b> , 93,	3.3	50
165	Robust Phonon-Plasmon Coupling in Quasifreestanding Graphene on Silicon Carbide. <i>Physical Review Letters</i> , <b>2016</b> , 116, 106802	7.4	21
164	Porous Ge@C materials via twin polymerization of germanium(II) salicyl alcoholates for Li-ion batteries. <i>Journal of Materials Chemistry A</i> , <b>2016</b> , 4, 2705-2719	13	19
163	Nickel enhanced graphene growth directly on dielectric substrates by molecular beam epitaxy. <i>Journal of Applied Physics</i> , <b>2016</b> , 120, 045309	2.5	7
162	Comeback of epitaxial graphene for electronics: large-area growth of bilayer-free graphene on SiC. <i>2D Materials</i> , <b>2016</b> , 3, 041002	5.9	95
161	Rashba splitting of 100 meV in Au-intercalated graphene on SiC. <i>Applied Physics Letters</i> , <b>2016</b> , 108, 1724054	9.4	15
160	Structural Changes in 2D BiSe Bilayers as n Increases in (BiSe)(NbSe) (n = 1-4) Heterostructures. <i>ACS Nano</i> , <b>2016</b> , 10, 9489-9499	16.7	11
159	Manifestation of nonlocal electron-electron interaction in graphene. <i>Physical Review B</i> , <b>2016</b> , 94,	3.3	11
158	Ramifications of optical pumping on the interpretation of time-resolved photoemission experiments on graphene. <i>Journal of Electron Spectroscopy and Related Phenomena</i> , <b>2015</b> , 200, 340-346	1.7	18
157	Ultrafast electron dynamics in epitaxial graphene investigated with time- and angle-resolved photoemission spectroscopy. <i>Journal of Physics Condensed Matter</i> , <b>2015</b> , 27, 164206	1.8	27

156	Tunable carrier multiplication and cooling in graphene. <i>Nano Letters</i> , <b>2015</b> , 15, 326-31	11.5	64
155	Science and technology roadmap for graphene, related two-dimensional crystals, and hybrid systems. <i>Nanoscale</i> , <b>2015</b> , 7, 4598-810	7.7	2015
154	A universal transfer route for graphene. <i>Nanoscale</i> , <b>2014</b> , 6, 889-96	7.7	46
153	Luminescence, patterned metallic regions, and photon-mediated electronic changes in single-sided fluorinated graphene sheets. <i>ACS Nano</i> , <b>2014</b> , 8, 7801-8	16.7	22
152	Quasi-freestanding epitaxial graphene transistor with silicon nitride top gate. <i>Journal Physics D: Applied Physics</i> , <b>2014</b> , 47, 305103	3	5
151	Surface-induced hybridization between graphene and titanium. <i>ACS Nano</i> , <b>2014</b> , 8, 7704-13	16.7	33
150	Experimental analysis of the thermal annealing of hard a-C:H films. <i>Diamond and Related Materials</i> , <b>2014</b> , 45, 43-57	3.5	21
149	Ultrafast dynamics of massive dirac fermions in bilayer graphene. <i>Physical Review Letters</i> , <b>2014</b> , 112, 257401	7.4	82
148	The Hall coefficient: a tool for characterizing graphene field effect transistors. <i>2D Materials</i> , <b>2014</b> , 1, 035004	5.9	2
147	Polarization doping of graphene on silicon carbide. <i>2D Materials</i> , <b>2014</b> , 1, 035003	5.9	66
146	Healing of graphene on single crystalline Ni(111) films. <i>Applied Physics Letters</i> , <b>2014</b> , 105, 191612	3.4	13
145	Development and character of gap states on alkali doping of molecular films. <i>New Journal of Physics</i> , <b>2014</b> , 16, 023011	2.9	27
144	Backside Monitoring of Graphene on Silicon Carbide by Raman Spectroscopy. <i>Materials Science Forum</i> , <b>2014</b> , 778-780, 1166-1169	0.4	
143	Buffer layer free graphene on SiC(0 0 0 1) via interface oxidation in water vapor. <i>Carbon</i> , <b>2014</b> , 70, 258-265	15.4	37
142	Direct growth of quasi-free-standing epitaxial graphene on nonpolar SiC surfaces. <i>Physical Review B</i> , <b>2013</b> , 88,	3.3	38
141	Coexisting massive and massless Dirac fermions in symmetry-broken bilayer graphene. <i>Nature Materials</i> , <b>2013</b> , 12, 887-92	27	127
140	Spin-resolved photoemission and ab initio theory of graphene/SiC. <i>Physical Review B</i> , <b>2013</b> , 88,	3.3	11
139	Tuning the charge carriers in epitaxial graphene on SiC(0001) from electron to hole via molecular doping with C60F48. <i>Applied Physics Letters</i> , <b>2013</b> , 102, 241601	3.4	25

138	Observation of 4 nm pitch stripe domains formed by exposing graphene to ambient air. <i>ACS Nano</i> , <b>2013</b> , 7, 10032-7	16.7	35
137	Epitaxial Growth and Electronic Properties of Large Hexagonal Graphene Domains on Cu(111) Thin Film. <i>Applied Physics Express</i> , <b>2013</b> , 6, 075101	2.4	65
136	Strong plasmon reflection at nanometer-size gaps in monolayer graphene on SiC. <i>Nano Letters</i> , <b>2013</b> , 13, 6210-5	11.5	85
135	On the way to graphane-pronounced fluorescence of polyhydrogenated graphene. <i>Angewandte Chemie - International Edition</i> , <b>2013</b> , 52, 754-7	16.4	97
134	Looking behind the scenes: Raman spectroscopy of top-gated epitaxial graphene through the substrate. <i>New Journal of Physics</i> , <b>2013</b> , 15, 113006	2.9	17
133	Mono- and few-layer nanocrystalline graphene grown on Al <sub>2</sub> O <sub>3</sub> (0 0 0 1) by molecular beam epitaxy. <i>Carbon</i> , <b>2013</b> , 56, 339-350	10.4	51
132	Friction and atomic-layer-scale wear of graphitic lubricants on SiC(0001) in dry sliding. <i>Wear</i> , <b>2013</b> , 300, 78-81	3.5	38
131	Formation of high-quality quasi-free-standing bilayer graphene on SiC(0001) by oxygen intercalation upon annealing in air. <i>Carbon</i> , <b>2013</b> , 52, 83-89	10.4	92
130	Localized states influence spin transport in epitaxial graphene. <i>Physical Review Letters</i> , <b>2013</b> , 110, 067209	7.4	49
129	Robust graphene membranes in a silicon carbide frame. <i>ACS Nano</i> , <b>2013</b> , 7, 4441-8	16.7	15
128	Annealing-induced magnetic moments detected by spin precession measurements in epitaxial graphene on SiC. <i>Physical Review B</i> , <b>2013</b> , 87,	3.3	24
127	Growth and electronic structure of boron-doped graphene. <i>Physical Review B</i> , <b>2013</b> , 87,	3.3	96
126	Electron-phonon coupling in quasi-free-standing graphene. <i>Journal of Physics Condensed Matter</i> , <b>2013</b> , 25, 094001	1.8	21
125	Direct view of hot carrier dynamics in graphene. <i>Physical Review Letters</i> , <b>2013</b> , 111, 027403	7.4	260
124	Fabry-Perot enhanced Faraday rotation in graphene. <i>Optics Express</i> , <b>2013</b> , 21, 24736-41	3.3	44
123	Small scale rotational disorder observed in epitaxial graphene on SiC(0001). <i>New Journal of Physics</i> , <b>2013</b> , 15, 023019	2.9	7
122	Structural investigation of nanocrystalline graphene grown on (6B 6B)R30°-reconstructed SiC surfaces by molecular beam epitaxy. <i>New Journal of Physics</i> , <b>2013</b> , 15, 123034	2.9	13
121	Contribution of the buffer layer to the Raman spectrum of epitaxial graphene on SiC(0001). <i>New Journal of Physics</i> , <b>2013</b> , 15, 043031	2.9	75

120	Silicon Nitride as Top Gate Dielectric for Epitaxial Graphene. <i>Materials Science Forum</i> , <b>2013</b> , 740-742, 149-152	0.4	1
119	Detecting the local transport properties and the dimensionality of transport of epitaxial graphene by a multi-point probe approach. <i>Applied Physics Letters</i> , <b>2013</b> , 102, 033110	3.4	10
118	Visualizing atomic-scale negative differential resistance in bilayer graphene. <i>Physical Review Letters</i> , <b>2013</b> , 110, 036804	7.4	18
117	Growth and electronic structure of nitrogen-doped graphene on Ni(111). <i>Physical Review B</i> , <b>2012</b> , 86,	3.3	73
116	Classical to quantum crossover of the cyclotron resonance in graphene: a study of the strength of intraband absorption. <i>New Journal of Physics</i> , <b>2012</b> , 14, 095008	2.9	23
115	Quantitative multichannel NC-AFM data analysis of graphene growth on SiC(0001). <i>Beilstein Journal of Nanotechnology</i> , <b>2012</b> , 3, 179-85	3	17
114	Implanted bottom gate for epitaxial graphene on silicon carbide. <i>Journal Physics D: Applied Physics</i> , <b>2012</b> , 45, 154006	3	5
113	Decoupling the Graphene Buffer Layer from SiC(0001) via Interface Oxidation. <i>Materials Science Forum</i> , <b>2012</b> , 717-720, 649-652	0.4	15
112	Long spin relaxation times in wafer scale epitaxial graphene on SiC(0001). <i>Nano Letters</i> , <b>2012</b> , 12, 1498-5025	10.25	102
111	Intrinsic terahertz plasmons and magnetoplasmons in large scale monolayer graphene. <i>Nano Letters</i> , <b>2012</b> , 12, 2470-4	11.5	191
110	Precise control of epitaxy of graphene by microfabricating SiC substrate. <i>Applied Physics Letters</i> , <b>2012</b> , 101, 041605	3.4	25
109	Influence of structural properties on ballistic transport in nanoscale epitaxial graphene cross junctions. <i>Nanotechnology</i> , <b>2012</b> , 23, 395203	3.4	4
108	Origin of doping in quasi-free-standing graphene on silicon carbide. <i>Physical Review Letters</i> , <b>2012</b> , 108, 246104	7.4	185
107	Gated Epitaxial Graphene Devices. <i>Materials Science Forum</i> , <b>2012</b> , 717-720, 675-678	0.4	
106	Highly p-doped epitaxial graphene obtained by fluorine intercalation. <i>Applied Physics Letters</i> , <b>2011</b> , 98, 184102	3.4	125
105	High-transconductance graphene solution-gated field effect transistors. <i>Applied Physics Letters</i> , <b>2011</b> , 99, 033503	3.4	71
104	Epitaxial Graphene on SiC(0001). <i>Nanoscience and Technology</i> , <b>2011</b> , 135-159	0.6	0
103	Bottom-gated epitaxial graphene. <i>Nature Materials</i> , <b>2011</b> , 10, 357-60	27	69

102	Giant Faraday rotation in single- and multilayer graphene. <i>Nature Physics</i> , <b>2011</b> , 7, 48-51	16.2	428
101	A momentum space view of the surface chemical bond. <i>Physical Chemistry Chemical Physics</i> , <b>2011</b> , 13, 3604-11	3.6	26
100	Multicomponent magneto-optical conductivity of multilayer graphene on SiC. <i>Physical Review B</i> , <b>2011</b> , 84,	3.3	40
99	Terahertz radiation driven chiral edge currents in graphene. <i>Physical Review Letters</i> , <b>2011</b> , 107, 276601	7.4	94
98	Effective screening and the plasmaron bands in graphene. <i>Physical Review B</i> , <b>2011</b> , 84,	3.3	78
97	The interaction of Xe and Xe+K with graphene. <i>Journal of Electron Spectroscopy and Related Phenomena</i> , <b>2011</b> , 183, 118-124	1.7	3
96	Transport properties of high-quality epitaxial graphene on 6H-SiC(0001). <i>Solid State Communications</i> , <b>2011</b> , 151, 1061-1064	1.6	18
95	The quasi-free-standing nature of graphene on H-saturated SiC(0001). <i>Applied Physics Letters</i> , <b>2011</b> , 99, 122106	3.4	206
94	Strain and Charge in Epitaxial Graphene on Silicon Carbide Studied by Raman Spectroscopy. <i>Materials Science Forum</i> , <b>2010</b> , 645-648, 603-606	0.4	11
93	Transport Properties of Single-Layer Epitaxial Graphene on 6H-SiC (0001). <i>Materials Science Forum</i> , <b>2010</b> , 645-648, 637-641	0.4	5
92	Quantum oscillations and quantum Hall effect in epitaxial graphene. <i>Physical Review B</i> , <b>2010</b> , 81,	3.3	155
91	Characteristics of solution gated field effect transistors on the basis of epitaxial graphene on silicon carbide. <i>Journal Physics D: Applied Physics</i> , <b>2010</b> , 43, 345303	3	41
90	The interaction of quasi-particles in graphene with chemical dopants. <i>New Journal of Physics</i> , <b>2010</b> , 12, 125014	2.9	9
89	Extended van Hove singularity and superconducting instability in doped graphene. <i>Physical Review Letters</i> , <b>2010</b> , 104, 136803	7.4	232
88	Observation of plasmarons in quasi-freestanding doped graphene. <i>Science</i> , <b>2010</b> , 328, 999-1002	33.3	340
87	Quasi-Freestanding Graphene on SiC(0001). <i>Materials Science Forum</i> , <b>2010</b> , 645-648, 629-632	0.4	42
86	Epitaxial Graphenes on Silicon Carbide. <i>MRS Bulletin</i> , <b>2010</b> , 35, 296-305	3.2	164
85	Strong phonon-plasmon coupled modes in the graphene/silicon carbide heterosystem. <i>Physical Review B</i> , <b>2010</b> , 82,	3.3	81



84	Influence of the growth conditions of epitaxial graphene on the film topography and the electron transport properties. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2010</b> , 42, 687-690	3	13
83	Automated preparation of high-quality epitaxial graphene on 6H-SiC(0001). <i>Physica Status Solidi (B): Basic Research</i> , <b>2010</b> , 247, 2924-2926	1.3	52
82	HREELS study of graphene formed on hexagonal silicon carbide. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2010</b> , 7, 394-397		8
81	Atomic layer deposited aluminum oxide films on graphite and graphene studied by XPS and AFM. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2010</b> , 7, 398-401		39
80	Friction and dissipation in epitaxial graphene films. <i>Physical Review Letters</i> , <b>2009</b> , 102, 086102	7.4	412
79	Low-temperature ballistic transport in nanoscale epitaxial graphene cross junctions. <i>Applied Physics Letters</i> , <b>2009</b> , 95, 262101	3.4	23
78	Photoemission of Ga <sub>1-x</sub> Mn <sub>x</sub> As with high Curie temperature and transformation into MnAs of zincblende structure. <i>Physica Status Solidi (B): Basic Research</i> , <b>2009</b> , 246, 1435-1439	1.3	7
77	Towards wafer-size graphene layers by atmospheric pressure graphitization of silicon carbide. <i>Nature Materials</i> , <b>2009</b> , 8, 203-7	27	2132
76	The electronic structure of pentacene revisited. <i>Journal of Electron Spectroscopy and Related Phenomena</i> , <b>2009</b> , 174, 22-27	1.7	18
75	Experimental studies of the electronic structure of graphene. <i>Progress in Surface Science</i> , <b>2009</b> , 84, 380-416	4.6	59
74	Quasiparticle transformation during a metal-insulator transition in graphene. <i>Physical Review Letters</i> , <b>2009</b> , 103, 056404	7.4	187
73	Reconstruction of molecular orbital densities from photoemission data. <i>Science</i> , <b>2009</b> , 326, 702-6	33.3	224
72	Raman topography and strain uniformity of large-area epitaxial graphene. <i>Nano Letters</i> , <b>2009</b> , 9, 964-8	11.5	138
71	Origin of the energy bandgap in epitaxial graphene. <i>Nature Materials</i> , <b>2008</b> , 7, 258-9; author reply 259-60	7	152
70	Atomic and electronic structure of few-layer graphene on SiC(0001) studied with scanning tunneling microscopy and spectroscopy. <i>Physical Review B</i> , <b>2008</b> , 77,	3.3	314
69	Local work function measurements of epitaxial graphene. <i>Applied Physics Letters</i> , <b>2008</b> , 93, 133117	3.4	186
68	Raman spectra of epitaxial graphene on SiC(0001). <i>Applied Physics Letters</i> , <b>2008</b> , 92, 201918	3.4	276
67	Morphology of graphene thin film growth on SiC(0001). <i>New Journal of Physics</i> , <b>2008</b> , 10, 023034	2.9	147



66	Graphene Layers on Silicon Carbide Studied by Raman Spectroscopy. <i>Materials Science Forum</i> , <b>2008</b> , 600-603, 567-570	0.4	2
65	Interface-induced complex electronic interference structures in Ag films on Ge(111). <i>Physical Review B</i> , <b>2008</b> , 78,	3.3	16
64	Morphology and electronic properties of metal organic molecular beam epitaxy grown ZnO on hydrogen passivated 6H-SiC(0001)a). <i>Journal of Applied Physics</i> , <b>2008</b> , 103, 103720	2.5	10
63	Alternative techniques to reduce interface traps in n-type 4H-SiC MOS capacitors. <i>Physica Status Solidi (B): Basic Research</i> , <b>2008</b> , 245, 1378-1389	1.3	56
62	Effect of an intermediate graphite layer on the electronic properties of metal/SiC contacts. <i>Physica Status Solidi (B): Basic Research</i> , <b>2008</b> , 245, 1369-1377	1.3	30
61	Epitaxial graphene: a new material. <i>Physica Status Solidi (B): Basic Research</i> , <b>2008</b> , 245, 1436-1446	1.3	150
60	Molecular and electronic structure of PTCDA on bilayer graphene on SiC(0001) studied with scanning tunneling microscopy. <i>Physica Status Solidi (B): Basic Research</i> , <b>2008</b> , 245, 2064-2067	1.3	49
59	Interaction, growth, and ordering of epitaxial graphene on SiC{0001} surfaces: A comparative photoelectron spectroscopy study. <i>Physical Review B</i> , <b>2008</b> , 77,	3.3	759
58	Plasmon dispersion and damping in electrically isolated two-dimensional charge sheets. <i>Physical Review B</i> , <b>2008</b> , 78,	3.3	192
57	Photoemission Studies of Graphene on SiC: Growth, Interface, and Electronic Structure <b>2008</b> , 159-170		21
56	Interlayer interaction and electronic screening in multilayer graphene investigated with angle-resolved photoemission spectroscopy. <i>Physical Review Letters</i> , <b>2007</b> , 98, 206802	7.4	612
55	Renormalization of graphene bands by many-body interactions. <i>Solid State Communications</i> , <b>2007</b> , 143, 63-71	1.6	63
54	Quasiparticle dynamics in graphene. <i>Nature Physics</i> , <b>2007</b> , 3, 36-40	16.2	932
53	Band structure and many body effects in graphene. <i>European Physical Journal: Special Topics</i> , <b>2007</b> , 148, 5-13	2.3	22
52	Quantum size effects in quasi-free-standing Pb layers. <i>Physical Review B</i> , <b>2007</b> , 75,	3.3	44
51	Electronic Structure of Graphite/6H-SiC Interfaces. <i>Materials Science Forum</i> , <b>2007</b> , 556-557, 701-704	0.4	14
50	Initial Stages of the Graphite-SiC(0001) Interface Formation Studied by Photoelectron Spectroscopy. <i>Materials Science Forum</i> , <b>2007</b> , 556-557, 525-528	0.4	49
49	4H-SiC Metal-Oxide-Semiconductor (MOS) Capacitors Fabricated by Oxidation in a Tungsten Lamp Furnace in Combination with a Microwave Plasma and Subsequent Deposition of Al <sub>2</sub> O <sub>3</sub> . <i>Materials Science Forum</i> , <b>2007</b> , 556-557, 627-630	0.4	2

48	Symmetry breaking in few layer graphene films. <i>New Journal of Physics</i> , <b>2007</b> , 9, 385-385	2.9	162
47	Thermal stability of surface and interface structure of atomic layer deposited Al <sub>2</sub> O <sub>3</sub> on H-terminated silicon. <i>Journal of Applied Physics</i> , <b>2007</b> , 102, 094503	2.5	17
46	Schottky barrier between 6H-SiC and graphite: Implications for metal/SiC contact formation. <i>Applied Physics Letters</i> , <b>2006</b> , 88, 242103	3.4	87
45	Correlation effects at ideal SiC{0001} $\overline{1}\overline{1}$ surfaces. <i>Physical Review B</i> , <b>2006</b> , 73,	3.3	22
44	Interface of atomic layer deposited Al <sub>2</sub> O <sub>3</sub> on H-terminated silicon. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2006</b> , 203, 2194-2199	1.6	11
43	How the solid state matrix affects the chemical shift of core-level binding energies: A novel method to take the induction effect into account. <i>Solid State Communications</i> , <b>2006</b> , 139, 370-375	1.6	2
42	Electronic properties of clean unreconstructed 6H-SiC(0001) surfaces studied by angle resolved photoelectron spectroscopy. <i>Surface Science</i> , <b>2006</b> , 600, 3845-3850	1.8	12
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40	Controlling the electronic structure of bilayer graphene. <i>Science</i> , <b>2006</b> , 313, 951-4	33.3	2717
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37	First results from a second generation toroidal electron spectrometer. <i>Journal of Electron Spectroscopy and Related Phenomena</i> , <b>2005</b> , 144-147, 1001-1004	1.7	53
36	ALD Deposited Al <sub>2</sub> O <sub>3</sub> Films on 6H-SiC(0001) after Annealing in Hydrogen Atmosphere. <i>Materials Science Forum</i> , <b>2005</b> , 483-485, 559-562	0.4	2
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34	Surface Band Structure Studies of Si Rich Reconstructions on 4H-SiC(1-100). <i>Materials Science Forum</i> , <b>2005</b> , 483-485, 547-550	0.4	4
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27	Stacking rearrangement at 6H-SiC(0001) surfaces during thermal hydrogenation. <i>Surface Science</i> , <b>2003</b> , 532-535, 698-704	1.8	7
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25	Doping of single-walled carbon nanotube bundles by Brønsted acids. <i>Physical Chemistry Chemical Physics</i> , <b>2003</b> , 5, 5472-5476	3.6	175
24	Al <sub>2</sub> O <sub>3</sub> prepared by atomic layer deposition as gate dielectric on 6H-SiC(0001). <i>Applied Physics Letters</i> , <b>2003</b> , 83, 1830-1832	3.4	90
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16	Preparation and Characterization of Hydrogen Terminated 6H-SiC. <i>Materials Science Forum</i> , <b>2001</b> , 353-356, 223-226	0.4	11
15	Electronic and chemical passivation of hexagonal 6H-SiC surfaces by hydrogen termination. <i>Applied Physics Letters</i> , <b>2001</b> , 78, 1216-1218	3.4	84
14	Surface, interface and bulk properties of GaAs(111)B treated by Se layers. <i>Journal Physics D: Applied Physics</i> , <b>2001</b> , 34, 678-682	3	
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12	The adsorption geometry of Ag(1 1 1)( $\sqrt{3}\sqrt{3}$ )R19.1°-4Ar studied by LEED. <i>Surface Science</i> , <b>2001</b> , 475, 89-95	1.8	14
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